CMSA150N04A

N-Channel Enhancement Mode Field Effect Transistor

General Description

The CMSA150N04A uses advanced technology to provide excellent RDS (ON) . This device is suitable to be used as the low side FET in SMPS,load switching and general purpose.

Product Summary

BVDSS	RDSON	ID
40V	2.9mΩ	100A

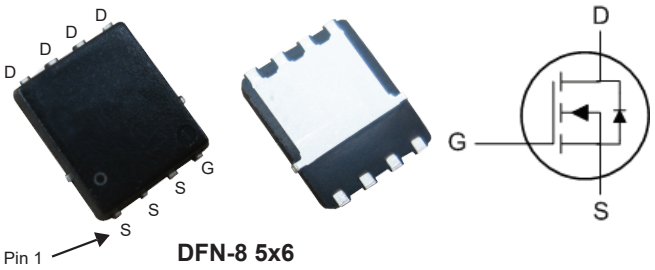
Applications

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

Features

- V_{DS} =40V,I_D =100A
  RDS(ON)=2.9mΩ (typical) @ V_{GS}=10V
  RDS(ON)=4.8mΩ (typical) @ V_{GS}=4.5V
- Very low on-resistance RDS(on)
- 100% avalanche tested
- RoHS Compliant

DFN-8 5x6 Pin Configuration



DFN-8 5x6

Type	Package	Marking
CMSA150N04A	DFN-8 5*6	CMSA150N04A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current	100	A
I_D@T_C=100℃		80	A
I_{DM}	Pulsed Drain Current	300	A
EAS	Single Pulse Avalanche Energy [1]	540	mJ
P_D@T_C=25℃	Total Power Dissipation	125	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	---	60	℃/W
$R_{\theta JC}$	Thermal Resistance Junction -Case	---	1.2	℃/W

Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250μA	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=20A	---	---	2.9	mΩ
		V_{GS}=4.5V, I_D=20A	---	---	4.8	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250μA	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=32V , V_{GS}=0V	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS} = ±16V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=20A	---	40	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.3	---	Ω
Q_g	Total Gate Charge	V_{DD}=20V , I_D=20A V_{GS}=10 V	---	43	---	nC
Q_{gs}	Gate-Source Charge		---	9	---	
Q_{gd}	Gate-Drain Charge		---	4	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=20V , V_{GS}=10V , R_G=3Ω R_L=1Ω	---	10	---	ns
T_r	Rise Time		---	4	---	
$T_{d(off)}$	Turn-Off Delay Time		---	33	---	
T_f	Fall Time		---	7	---	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1MHz	---	4600	---	pF
C_{oss}	Output Capacitance		---	920	---	
C_{rss}	Reverse Transfer Capacitance		---	45.5	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	V_G=V_D=0V , Force Current	---	---	100	A
$I_{S,pulse}$	Diode pulse current		---	---	300	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_s=20A , Tj=25℃	---	---	1.2	V

Notes

1. The test condition is V_{DS}=20V , V_{GS}=10V , L=1mH , I_D=33A.